Silicon N Channel MOS FET High Speed Power Switching

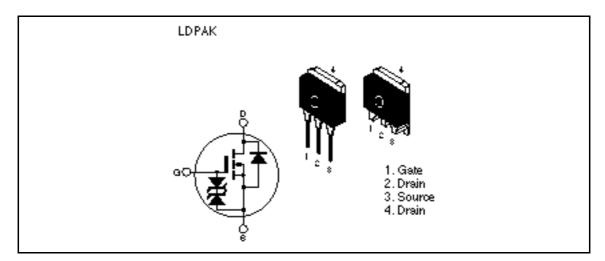
# HITACHI

ADE-208-567 Target specification 1st. Edition

### Features

- Low on-resistance
  - $R_{DS(on)} = 7m$  typ.
- 4V gate drive devices.
- High speed switching

### Outline





## **Absolute Maximum Ratings** (Ta = 25°C)

Item	Symbol	Ratings	Unit	
Drain to source voltage	V <sub>DSS</sub>	30	V	
Gate to source voltage	V <sub>GSS</sub>	±20	V	
Drain current	I <sub>D</sub>	50	А	
Drain peak current	↓ D(pulse) * 1	200	А	
Body to drain diode reverse drain current	l <sub>DR</sub>	50	А	
Channel dissipation	Pch* <sup>2</sup>	75	W	
Channel temperature	Tch	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

Notes: 1. PW 10µs, duty cycle 1 %

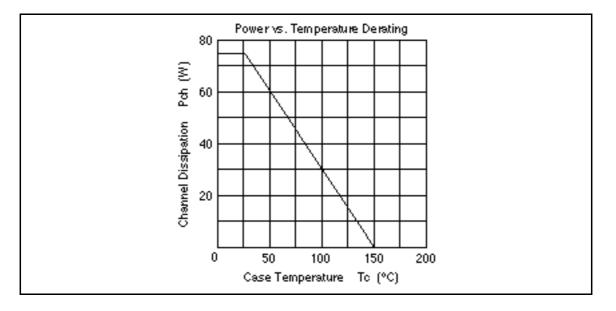
2. Value at  $Tc = 25^{\circ}C$ 

## **Electrical Characteristics** (Ta = 25°C)

Item	Symbol	Min	Тур	Мах	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	30	_	_	V	$I_{\rm D} = 10 {\rm mA}, V_{\rm GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	_	_	V	$I_{G} = \pm 100 \mu A, V_{DS} = 0$
Zero gate voltege drain current	I <sub>DSS</sub>	_	_	10	μA	$V_{\rm DS} = 30$ V, $V_{\rm GS} = 0$
Gate to source leak current	I <sub>GSS</sub>	_	_	±10	μA	$V_{GS} = \pm 16V, V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	_	2.0	V	$I_{\rm D} = 1$ mA, $V_{\rm DS} = 10$ V
Static drain to source on state	$R_{\text{DS(on)}}$	_	7.0	10	m	$I_{\rm D} = 25$ A, $V_{\rm GS} = 10$ V <sup>*1</sup>
resistance	R <sub>DS(on)</sub>	_	12	18	m	$I_{\rm D} = 25$ A, $V_{\rm GS} = 4$ V <sup>*1</sup>
Forward transfer admittance	y <sub>fs</sub>	25	45	_	S	$I_{\rm D} = 25$ A, $V_{\rm DS} = 10$ V <sup>*1</sup>
Input capacitance	Ciss	_	2000	_	pF	$V_{DS} = 10V$
Output capacitance	Coss	_	1500		pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	350		pF	f = 1MHz
Turn-on delay time	t <sub>d(on)</sub>	_	20		ns	$V_{GS} = 10V, I_{D} = 25A$
Rise time	t,	—	330		ns	$R_{L} = 0.4$
Turn-off delay time	$t_{d(off)}$	_	190		ns	_
Fall time	t <sub>f</sub>	_	190		ns	
Body to drain diode forward voltage	$V_{DF}$	_	0.95		V	$I_{\rm D} = 50$ A, $V_{\rm GS} = 0$
Body to drain diode reverse recovery time	t <sub>rr</sub>	_	140		ns	I <sub>F</sub> = 50A, V <sub>GS</sub> = 0 diF/ dt = 50A/μs
						$ur = 50A/\mu S$

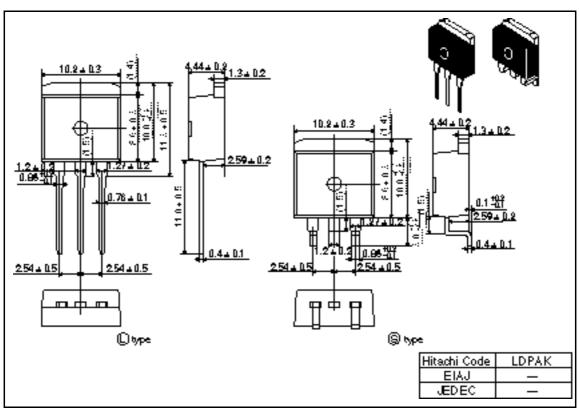
Note: 1. Pulse test

### **Main Characteristics**



## **Package Dimensions**





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